

Carbon-30: UHV-CVD Si:C @500C using 2% C₂H₄/He

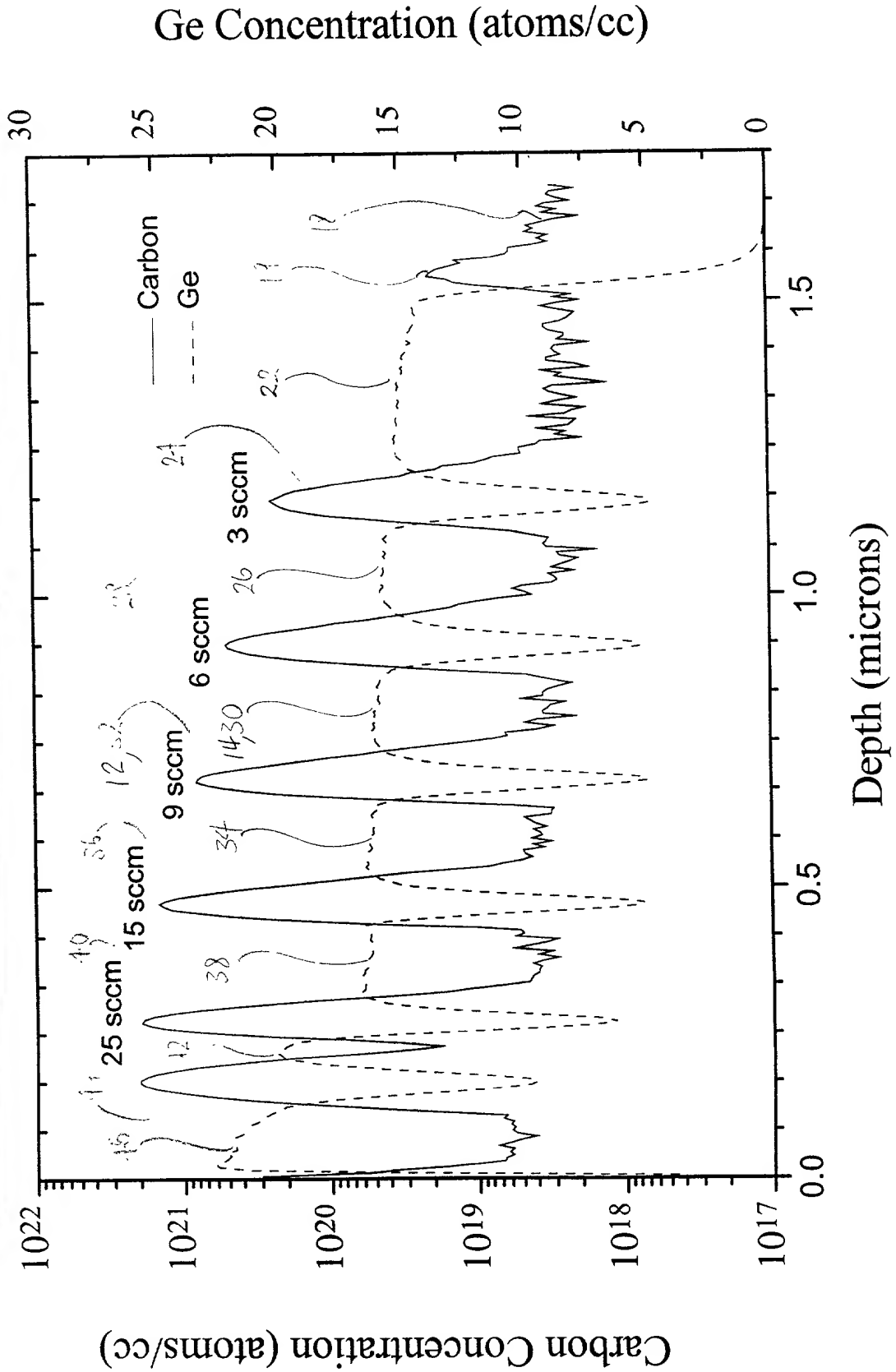


Figure 1

Carbon-30: UHV-CVD SiB:C @500C w/ 2% C₂H₄/He

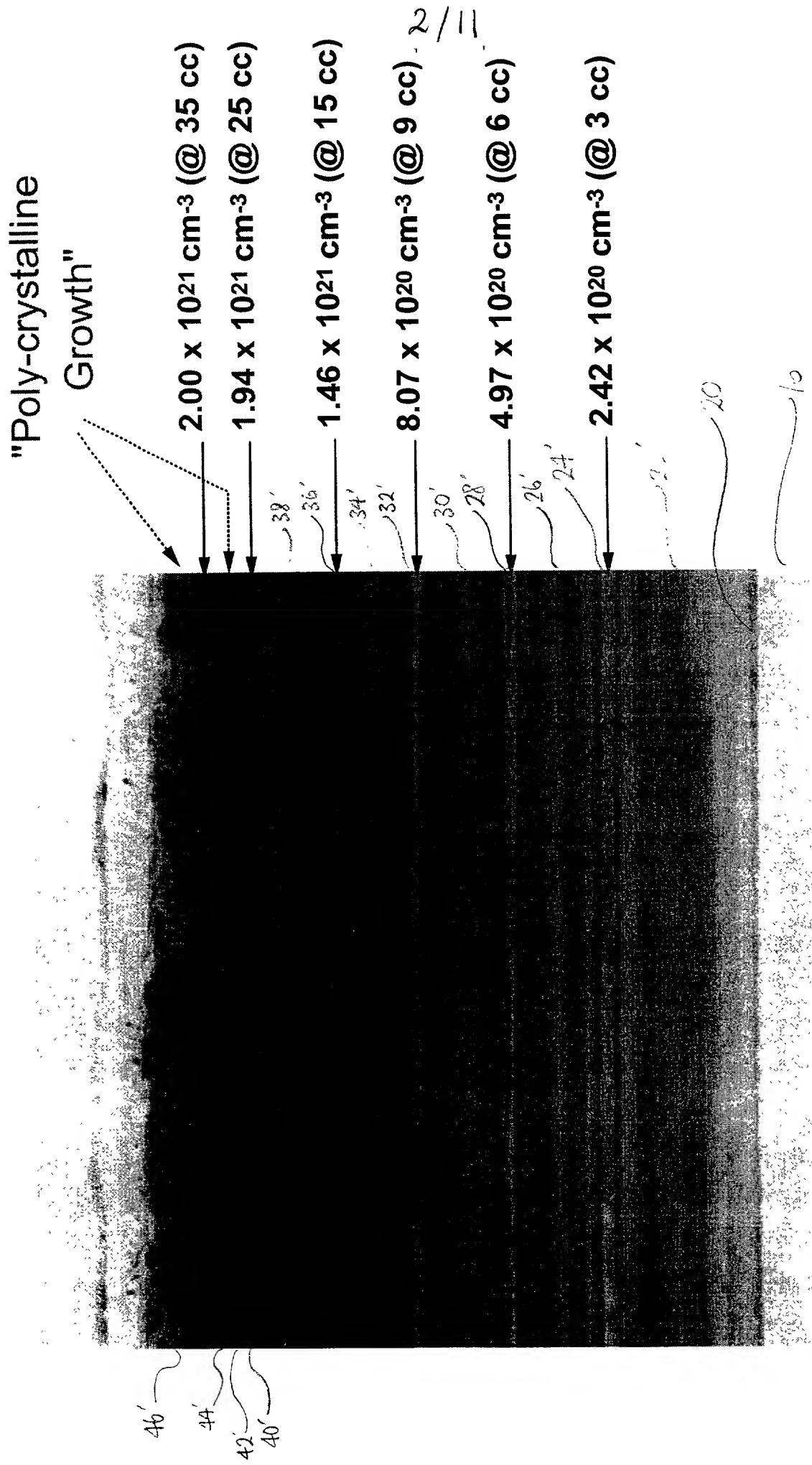
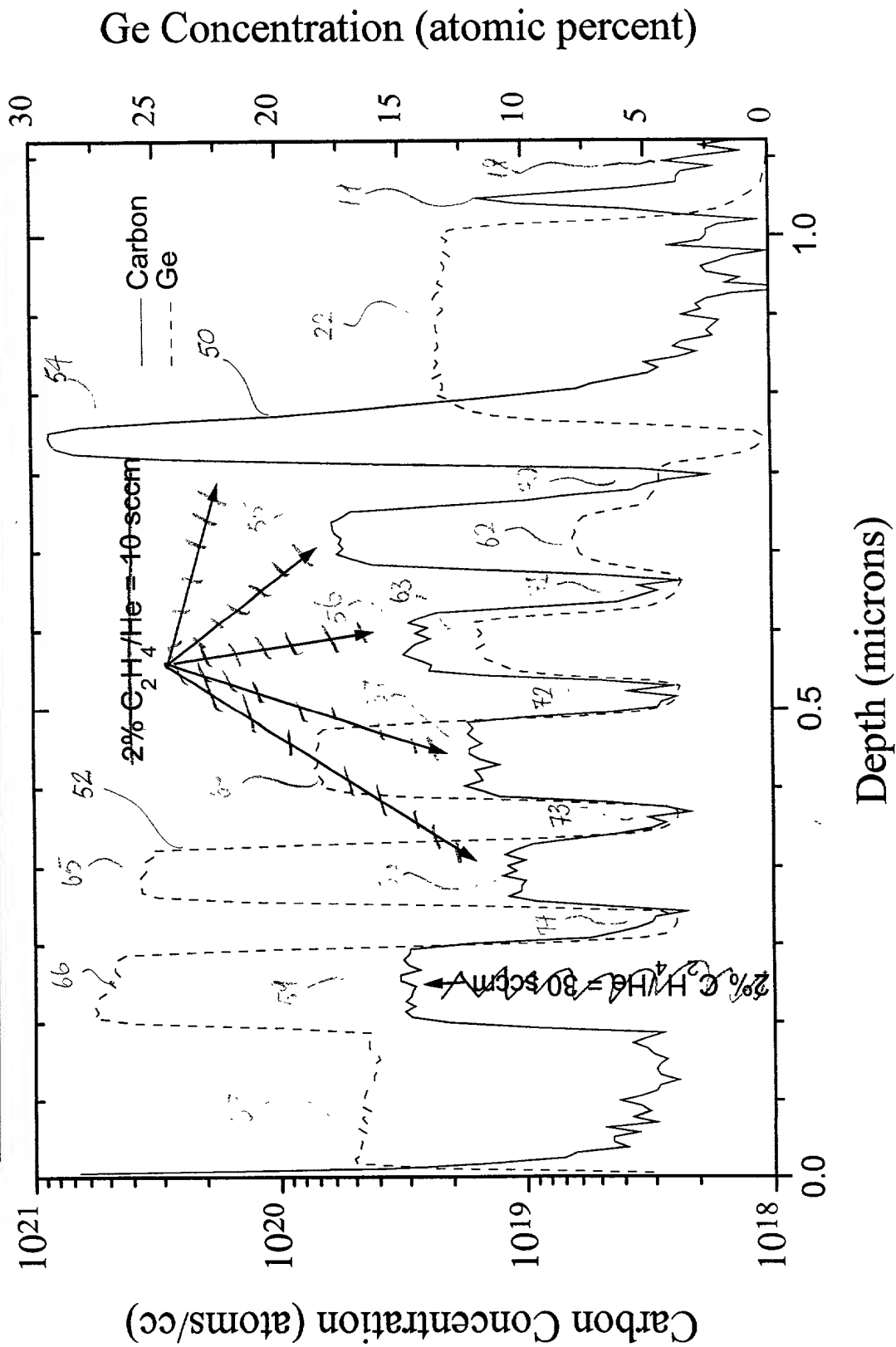


Figure 1

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~~Carbon-32: UHV-CVD-SiGeB:C @500C using 2% C₂H₄/He~~



Variable	Mean	Standard deviation	Minimum	Maximum	Skewness	Kurtosis	Normality test
Age	34.5	10.5	20	65	0.1	3.0	0.95
Gender	0.5	0.5	0	1	0.0	3.0	0.95
Marital status	0.6	0.5	0	1	0.0	3.0	0.95
Education	12.5	2.5	9	16	0.1	3.0	0.95
Income	1500	500	500	3000	0.1	3.0	0.95
Occupation	1.5	1.5	1	5	0.0	3.0	0.95
Health status	0.5	0.5	0	1	0.0	3.0	0.95
Stress level	2.5	1.5	1	5	0.1	3.0	0.95
Life satisfaction	3.5	1.5	1	5	0.1	3.0	0.95
Resilience	2.5	1.5	1	5	0.1	3.0	0.95
Optimism	3.5	1.5	1	5	0.1	3.0	0.95
Emotional stability	3.5	1.5	1	5	0.1	3.0	0.95
Self-efficacy	3.5	1.5	1	5	0.1	3.0	0.95
Life satisfaction	3.5	1.5	1	5	0.1	3.0	0.95
Resilience	2.5	1.5	1	5	0.1	3.0	0.95
Optimism	3.5	1.5	1	5	0.1	3.0	0.95
Emotional stability	3.5	1.5	1	5	0.1	3.0	0.95
Self-efficacy	3.5	1.5	1	5	0.1	3.0	0.95

~~Carbon-33: UHV-CVD SiGeB:C @500C using 1% C₂H₄/He~~

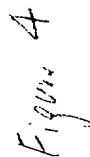
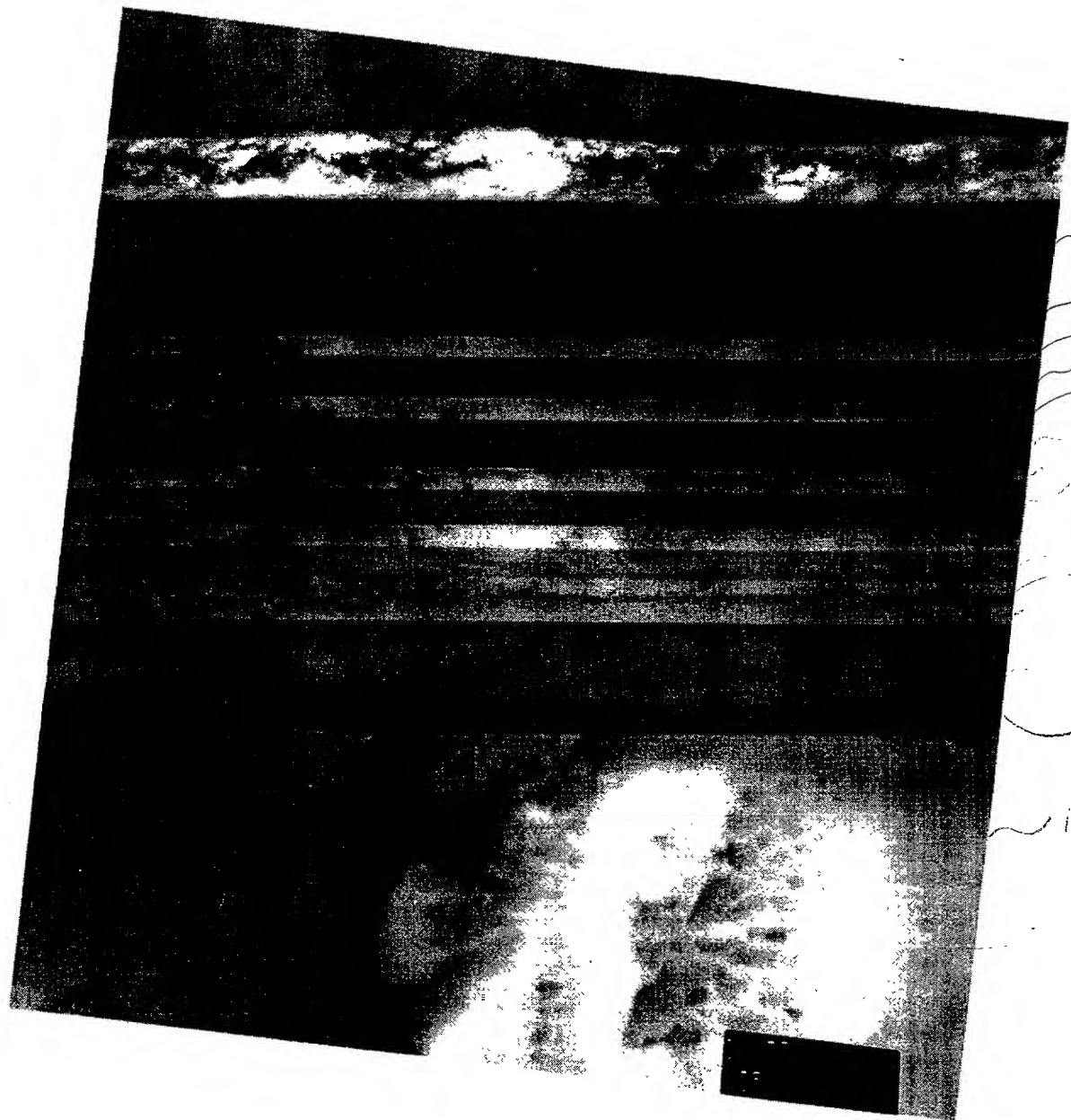


Figure 4

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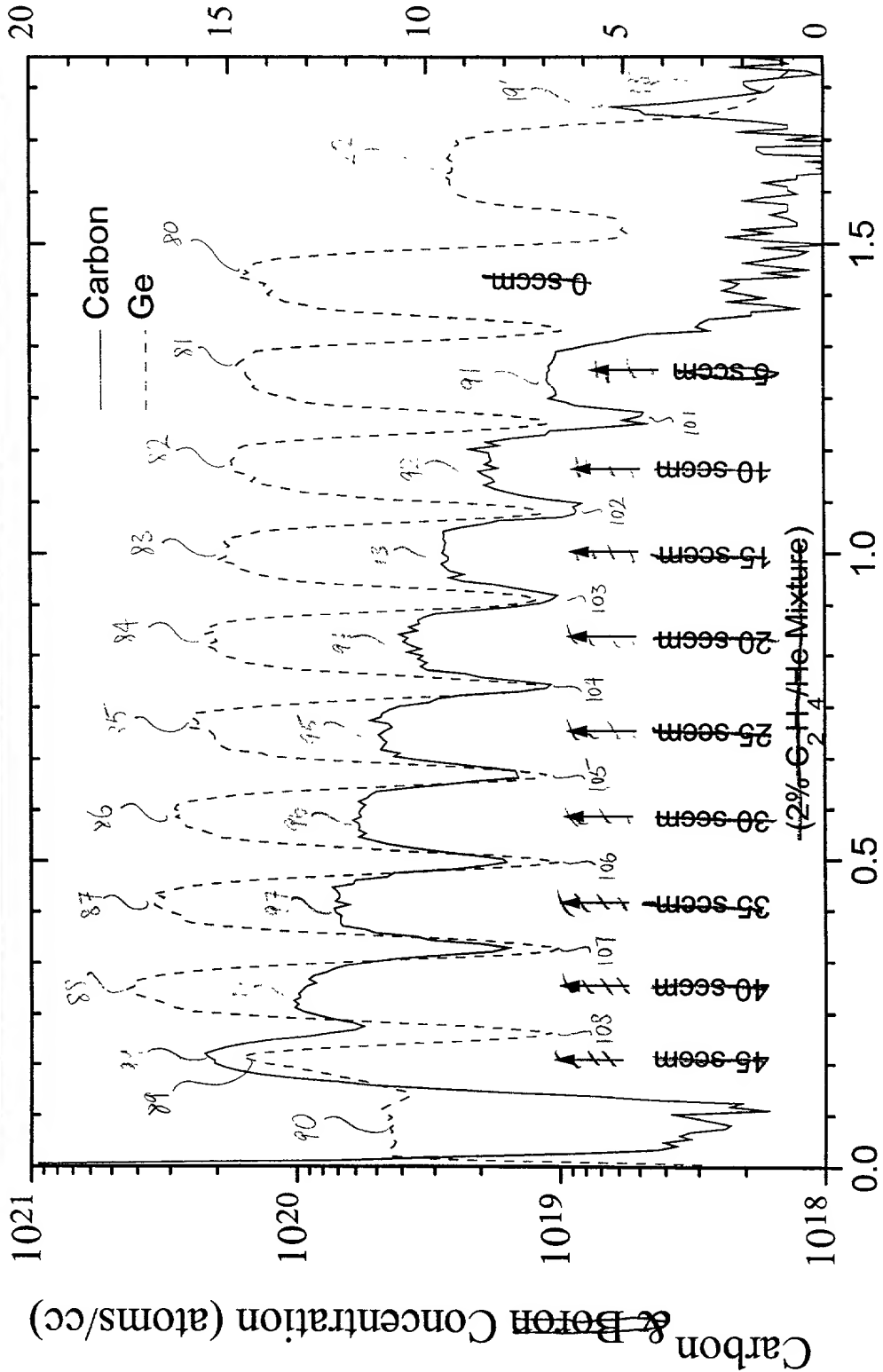
67"
59" 74"
58" 73"
59" 72"
57" 71"
20"
15"

Figure 5

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Ge Concentration (atoms percent)

Carbon 40: UHV-CVD SiGeB:C @500C using 2% C₂H₄/He



Depth (microns)

Figure 6

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~~UHV-CVD-SiC with 10% C₂H₆ (99%) & 100% C₂H₄ (99.5%)~~

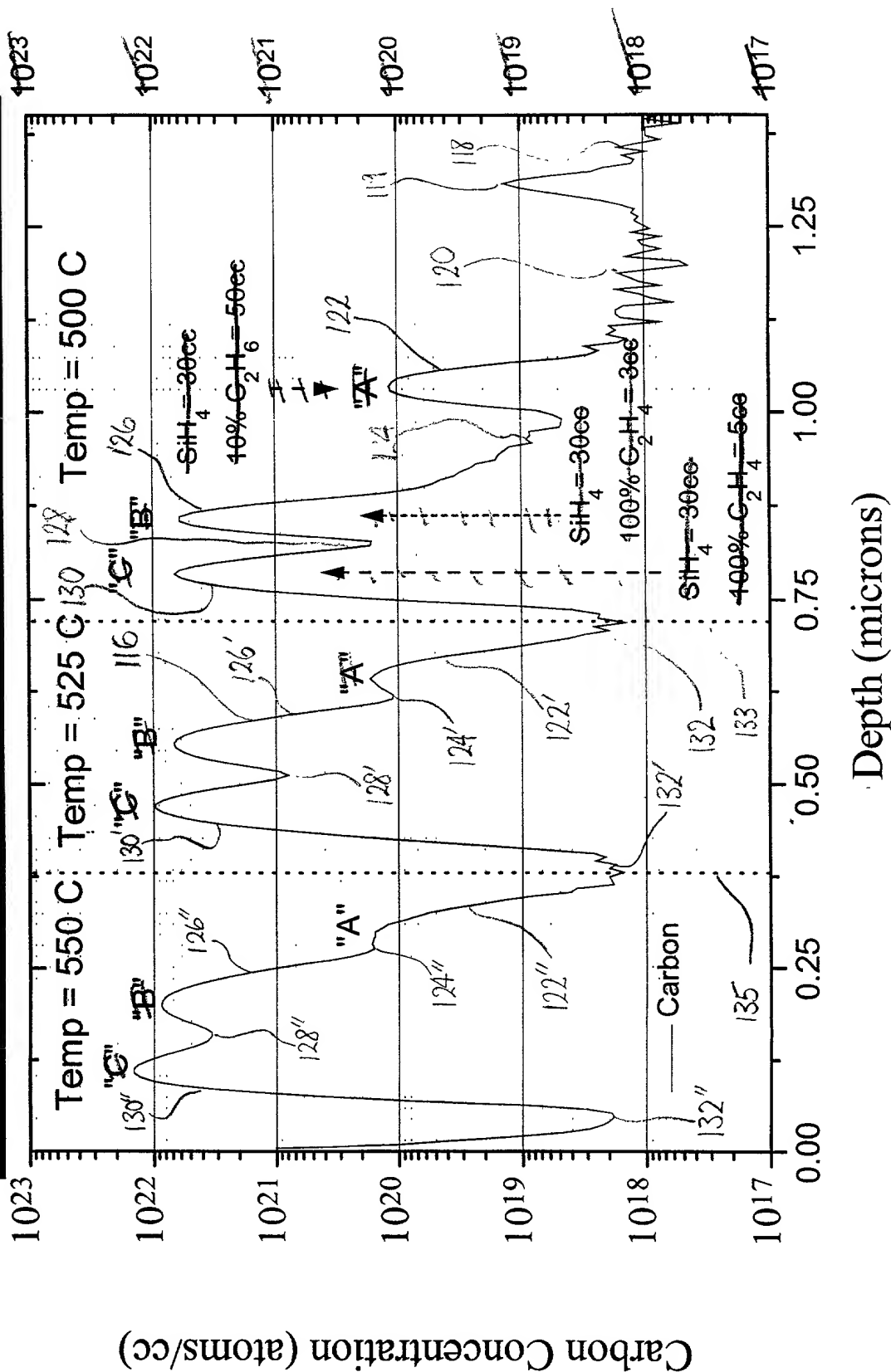
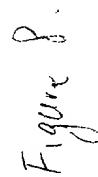


Figure 7

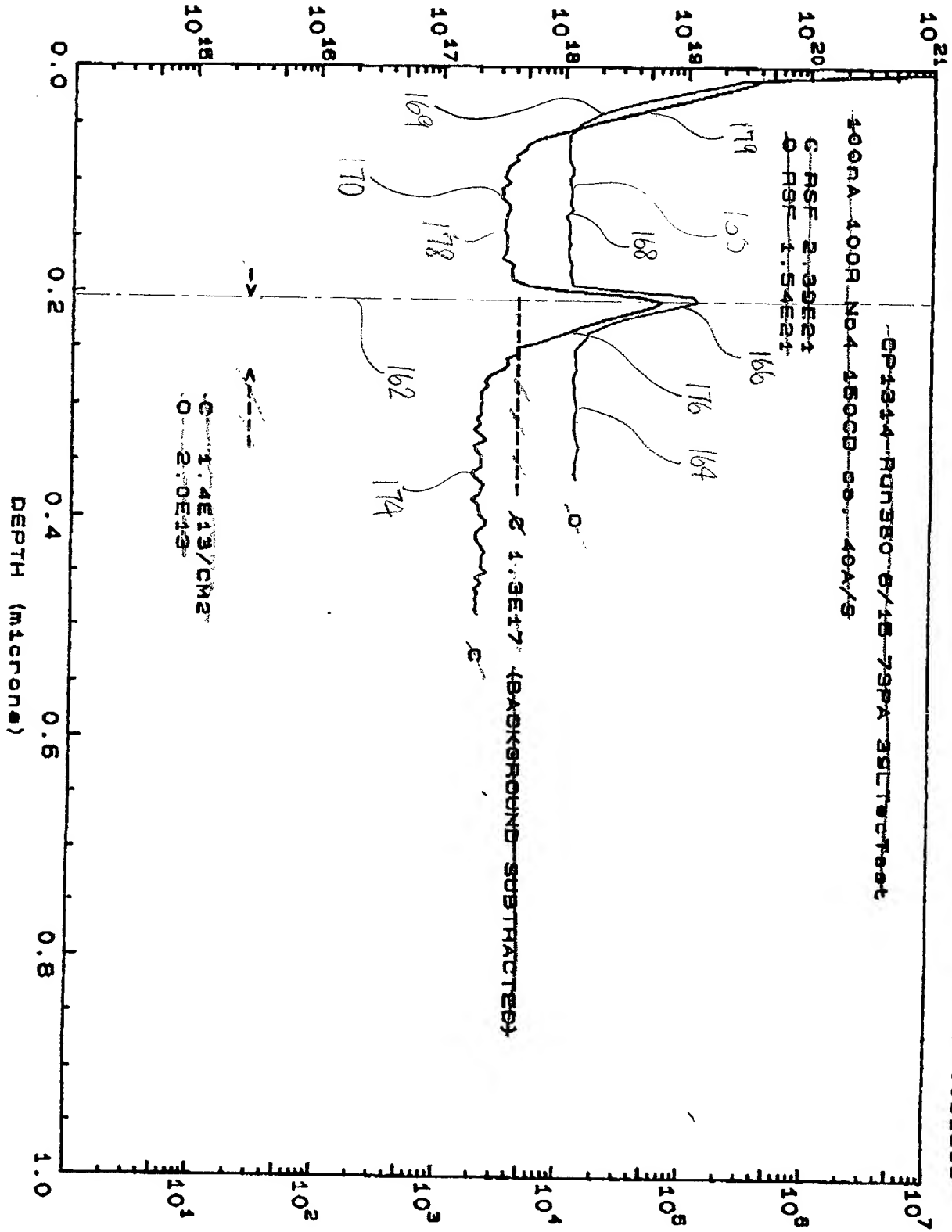


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CONCENTRATION (atoms/cc)

PROCESSED DATA
23 JUN 80 08

IBM Gemma-54 (V40/28)
FILE: 0081866



SECONDARY ION COUNTS

IBM 0081866
9

Carbon-13: UHV-CVD SiGeB:C at 550°C (C₂H₄) "As-Grown"

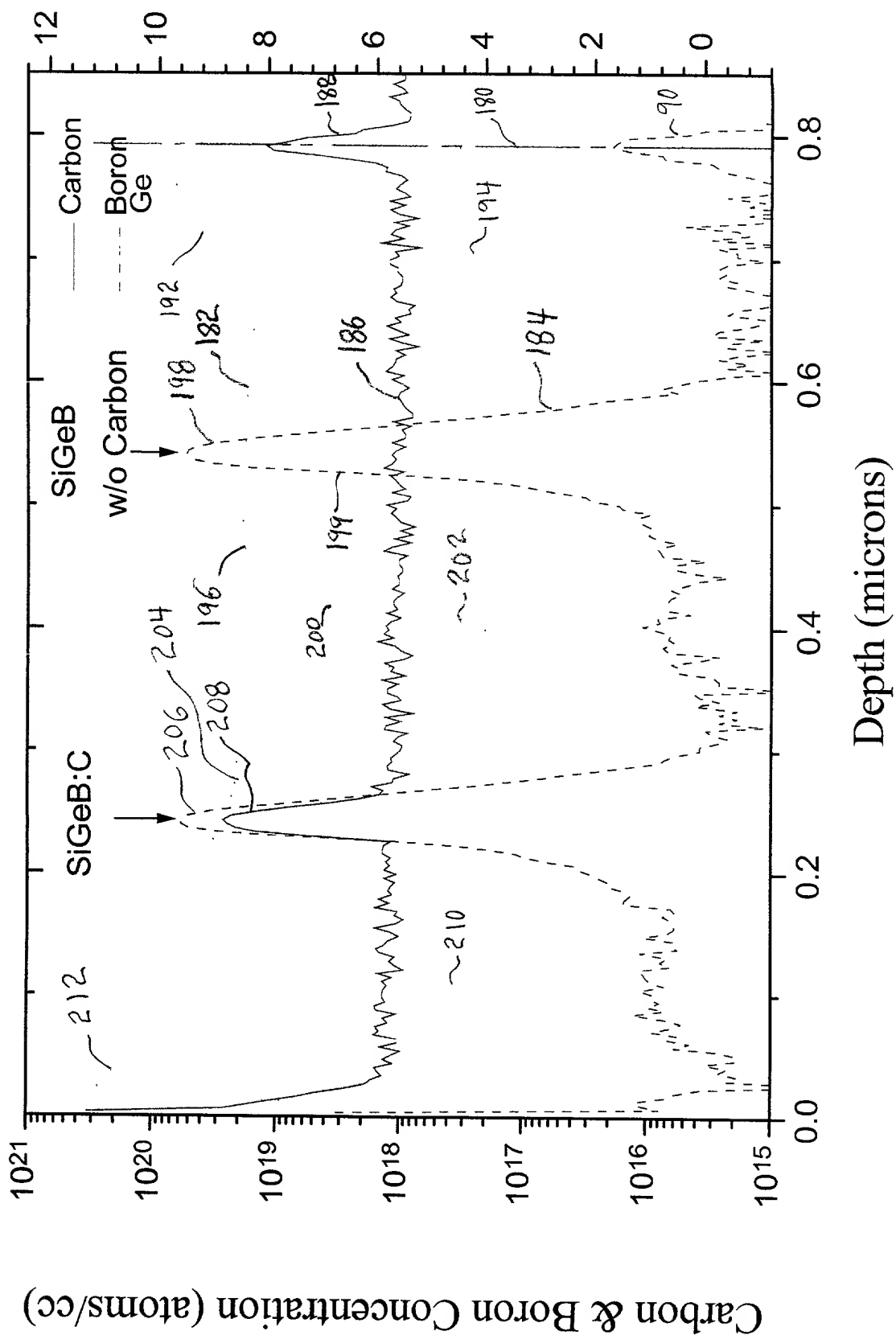


Figure 10

Impact of Carbon on SiGeB Layers after "850C Furnace Anneal"

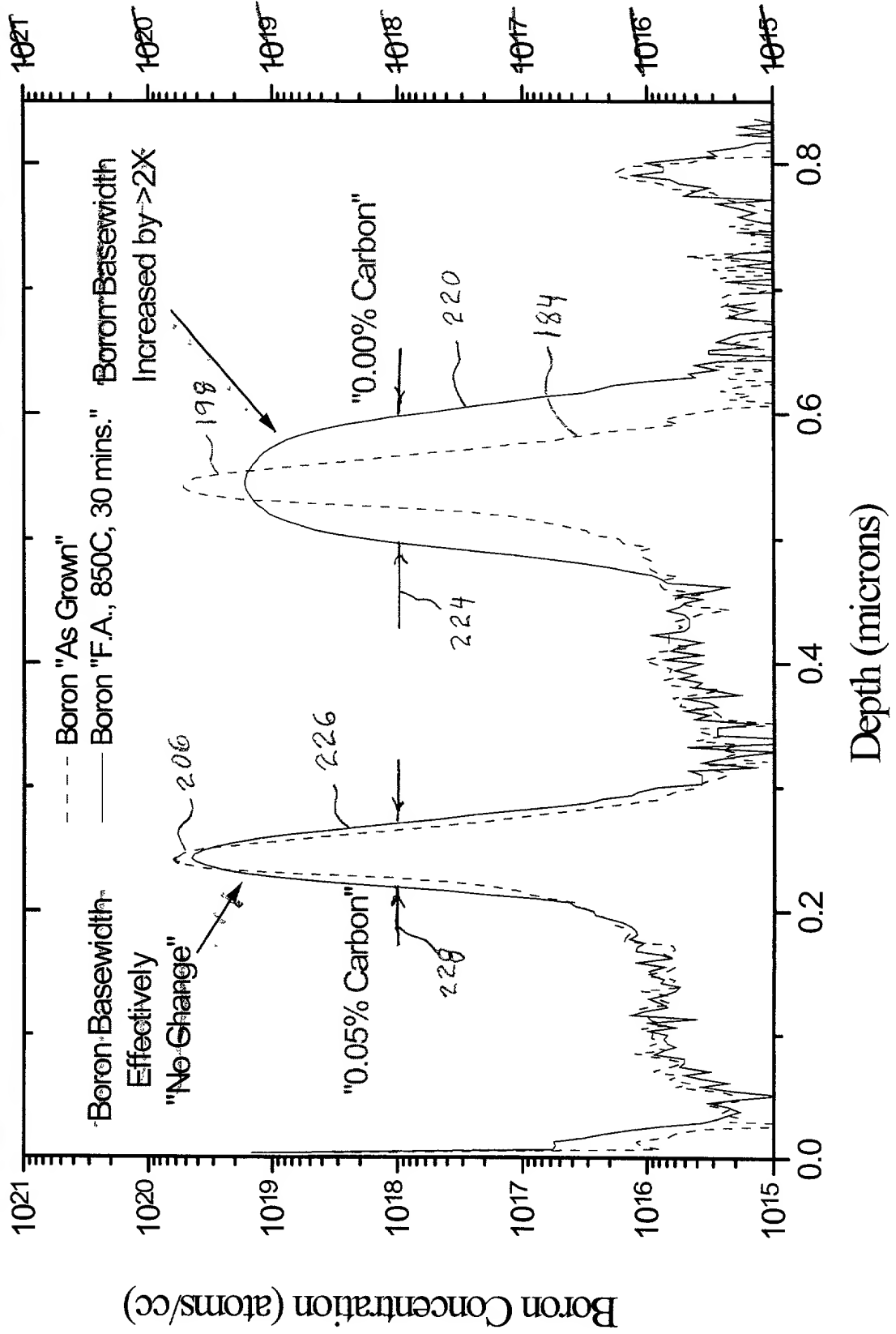


Figure 1